

SPIN TRANSFER TORQUE MEMORY CELLS

Abstract

Spin transfer torque memory cells and methods of forming the same are described herein. As an example, spin transfer torque memory cells may include an amorphous material, a storage material formed on the amorphous material, wherein the storage material is substantially boron free, an interfacial perpendicular magnetic anisotropy material formed on the storage material, a reference material formed on the interfacial perpendicular magnetic anisotropy material, wherein the reference material is substantially boron free, a buffer material formed on the reference material and a pinning material formed on the buffer material.

Fig. 1